

AMENDMENT TO THE CLAIMS:

1. (Currently Amended) An active-type light emitting display comprising:

a light emission panel including light emission elements each having a first electrode, a second electrode, and an emissive portion, and thin film transistors for respectively driving said light emission elements;

said light emission elements and at least one of said thin film transistor are formed on or above a same substrate;

said first electrode is electrically connected to at least one of said thin film transistors and is formed over an insulating layer, which is formed covering said at least one of said thin film transistors;

said second electrode is formed in a pattern that is common for a plurality of pixels, above said first electrode;

said thin film transistor includes a first conductive material that is formed between said substrate and said first electrode, said first conductive material is formed below said second electrode;

a connection conductor for connecting said second electrode and a signal supply portion, said signal supply portion supplying a signal to said second electrode for controlling said second electrode separately from said first electrode; and

said connection conductor having a section between said second electrode and said signal supply portion, at least a part of said section being a multilayer structure formed of a second electrode material used for said second electrode and a second conductive material used for said thin film transistors, said first conductive material is the same material as said second conductive material, said multilayer structure having a resistance lower than a resistance of a single layer of said second electrode material.

2. (Previously Presented) The active-type light emission display defined in Claim 1, wherein said conductive material used for said thin film transistors and said connection conductor comprises a material used for a gate electrode, a drain electrode, or a source electrode of each of said thin film transistors, or comprises an arbitrary combination of materials used for said gate electrode, said drain electrode and said source electrode thereof.

3. (Previously Presented) The active-type light emission display defined in Claim 1, wherein said conductive material used for said thin film transistors and said connection conductor comprises a metal material used for a gate electrode or drain electrode of each of said thin film transistors.

4. (Original) The active-type light emission display defined in Claim 1, wherein said second electrode comprises a common electrode spreading over substantially the whole of said panel.

5. (Original) The active-type light emission display defined in Claim 1, wherein said light emission element comprises an electroluminescent element in which an emissive layer is interposed between said first electrode and said second electrode.

6. (Original) The active-type light emission display defined in Claim 5, wherein said emissive layer comprises an organic compound having a luminous function.

7. (Original) The active-type light emission display defined in Claim 1, wherein an active layer of each of said thin film transistors comprises a polycrystalline silicon layer.

8. (Original) The active-type light emission display defined in Claim 1, wherein said signal supply portion comprises an external device connected to said light emission panel via terminals.

9. (Currently Amended) An active-type electroluminescent display comprising:
a light emission panel including light emission elements each having a first electrode, a second electrode, and a luminous portion, and thin film transistors for respectively driving said light emission elements;

said light emission elements and at least one of said thin film transistor are formed on or above a same substrate;

said first electrode is electrically connected to at least one of said thin film transistors and is formed over an insulating layer, which is formed covering said at least one of said thin film transistors;

said second electrode is formed in a pattern that is common for a plurality of pixels, above said first electrode;

said thin film transistor includes a first conductive material that is formed between said substrate and said first electrode, said first conductive material is formed below said second electrode;

a connection conductor for connecting said second electrode and a signal supply portion, said signal supply portion supplying a signal to said second electrode for controlling said second electrode separately from said first electrode; and

said connection conductor having a section between said second electrode and said signal supply portion, at least a part of said section being formed of a second conductive material-used for said thin film transistors, said first conductive material is the same material as said second conductive material, said part having a resistance lower than a resistance of a single layer of a material used for said second electrode.

10. (Previously Presented) The active-type electroluminescent display defined in Claim 9, wherein said conductive material used for said thin film transistors and said connection conductor comprises a material used for a gate electrode, a drain electrode, or a source electrode of each of said thin film transistors, or comprises an arbitrary combination of materials used for said gate electrode, said drain electrode and said source electrode thereof.

11. (Previously Presented) The active-type electroluminescent display defined in Claim 9, wherein said conductive material used for said thin film transistors and said connection conductor comprises a metal material used for a gate electrode or drain electrode of each of said thin film transistors.

12. (Previously Presented) The active-type electroluminescent display defined in Claim 9, wherein said second electrode comprises a common electrode spreading over substantially the whole of said panel.

13. (Previously Presented) The active-type electroluminescent display defined in Claim 9, wherein said light emission element comprises an electroluminescent element in which an emissive layer is interposed between said first electrode and said second electrode.

14. (Original) The active-type electroluminescent display defined in Claim 13, wherein said emissive layer comprises an organic compound having a luminous function.

15. (Original) The active-type electroluminescent display defined in Claim 9, wherein an active layer of each of said thin film transistors comprises a polycrystalline silicon layer.

16. (Original) The active-type electroluminescent display defined in Claim 9, wherein said signal supply portion comprises an external device connected to said light emission panel via terminals.

17. (Currently Amended) An active-type light emitting display comprising:
a light emission panel including light emission elements each having a first electrode, a second electrode, and an emissive portion, and thin film transistors for respectively driving said light emission elements;

said light emission elements and at least one of said thin film transistor are formed on or above a same substrate;

said first electrode is electrically connected to at least one of said thin film transistors and is formed over an insulating layer, which is formed covering said at least one of said thin film transistors;

said second electrode is formed in a pattern that is common for a plurality of pixels, above said first electrode; and

said thin film transistor includes a first conductive material that is formed between said substrate and said first electrode, said first conductive material is formed below said second electrode;

a connection conductor for connecting said second electrode and a signal supply portion, said signal supply portion supplying a signal to said second electrode for controlling said second electrode separately from said first electrode;

said connection conductor having a section between said second electrode and said signal supply portion, at least a part of said section being a multilayer structure formed of a second electrode material used for said second electrode and a second conductive material used for said thin film transistors, said first conductive material is the same material as said second conductive material, said multilayer structure having a resistance lower than a resistance of a single layer of said second electrode material.

18. (Currently Amended) An active-type electroluminescent display comprising:
a light emission panel including light emission elements each having a first electrode, a second electrode, and a luminous portion, and thin film transistors for respectively driving said light emission elements;

said light emission elements and at least one of said thin film transistor are formed on or above a same substrate;

said first electrode is electrically connected to at least one of said thin film transistors and is formed over an insulating layer, which is formed covering said at least one of said thin film transistors;

said second electrode is formed in a pattern that is common for a plurality of pixels, above said first electrode;

said thin film transistor includes a first conductive material that is formed between said substrate and said first electrode, said first conductive material is formed below said second electrode;

a connection conductor for connecting said second electrode and a signal supply portion, said signal supply portion supplying a signal to said second electrode for controlling said second electrode separately from said first electrode; and

said connection conductor having a section between said second electrode and said signal supply portion, at least a part of said section being formed of a second conductive material used for said thin-film transistors, said first conductive material is the same material as said second conductive material, said part having a resistance lower than a resistance of a single layer of a material used for said second electrode.